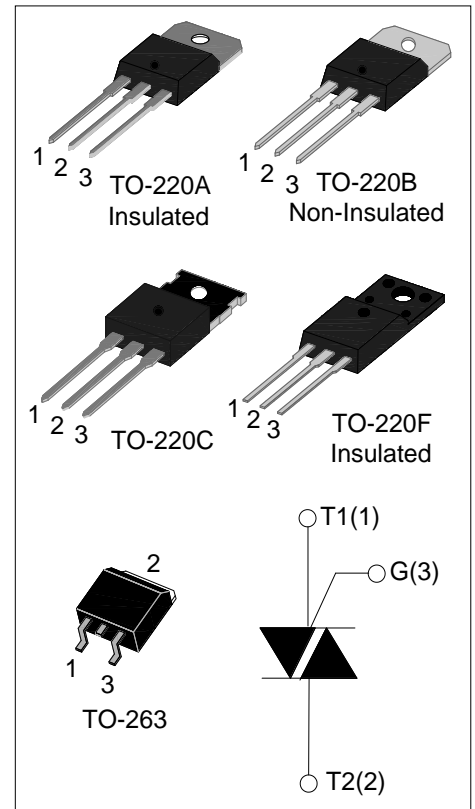


DESCRIPTION:

JST12 series triacs, with high ability to withstand the shock loading of large current, provide high dv/dt rate with strong resistance to electromagnetic interface. With high commutation performances, 3 quadrants products especially recommended for use on inductive load. JST12A provides insulation voltage rated at 2500V RMS and JST12F provides insulation voltage rated at 2000V RMS from all three terminals to external heatsink complying with UL standards (File ref: E252906).



MAIN FEATURES

Symbol	Value	Unit
$I_{T(RMS)}$	12	A
V_{DRM}/V_{RRM}	600 and 800 and 1200	V

ABSOLUTE MAXIMUM RATINGS

Parameter	Symbol	Value	Unit
Storage junction temperature range	T_{stg}	-40-150	°C
Operating junction temperature range	T_j	-40-125	°C
Repetitive peak off-state voltage ($T_j=25^{\circ}C$)	V_{DRM}	600/800/1200	V
Repetitive peak reverse voltage ($T_j=25^{\circ}C$)	V_{RRM}	600/800/1200	V
Non repetitive surge peak Off-state voltage	V_{DSM}	$V_{DRM} + 100$	V
Non repetitive peak reverse voltage	V_{RSM}	$V_{RRM} + 100$	V
RMS on-state current	TO-220A(Ins) ($T_C=90^{\circ}C$)	12	A
	TO-220B(Non-Ins)/ TO-220C($T_C=105^{\circ}C$)		
	TO-220F(Ins) ($T_C=79^{\circ}C$)		
	TO-263 ($T_C=115^{\circ}C$)		
Non repetitive surge peak on-state current (full cycle, F=50Hz)	I_{TSM}	120	A

JST12 Series

I ² t value for fusing (tp=10ms)	I ² t	72	A ² s
Critical rate of rise of on-state current (I _G =2×I _{GT})	di/dt	50	A/μs
Peak gate current	I _{GM}	4	A
Average gate power dissipation	P _{G(AV)}	1	W
Peak gate power	P _{GM}	5	W

ELECTRICAL CHARACTERISTICS (T_j=25°C unless otherwise specified)

3 Quadrants

Symbol	Test Condition	Quadrant		Value				Unit
				BW	CW	SW	TW	
I _{GT}	V _D =12V R _L =33Ω	I - II - III	MAX	50	35	10	5	mA
V _{GT}		I - II - III	MAX	1.3				V
V _{GD}	V _D =V _{DRM} T _j =125°C R _L =3.3KΩ	I - II - III	MIN	0.2				V
I _L	I _G =1.2I _{GT}	I - III	MAX	70	50	25	10	mA
		II		80	60	30	15	
I _H	I _T =100mA		MAX	60	40	15	10	mA
dV/dt	V _D =2/3V _{DRM} Gate Open T _j =125°C		MIN	1000	500	40	20	V/μs
(dV/dt) _c	without snubber T _j =125°C		MIN	12	6.5	5.0	3.5	V/μs

4 Quadrants

Symbol	Test Condition	Quadrant		Value		Unit
				B	C	
I _{GT}	V _D =12V R _L =33Ω	I - II - III	MAX	50	25	mA
		IV		70	50	
V _{GT}		ALL	MAX	1.3		V
V _{GD}	V _D =V _{DRM} T _j =125°C R _L =3.3KΩ	ALL	MIN	0.2		V
I _L	I _G =1.2I _{GT}	I - III - IV	MAX	50	40	mA
		II		100	80	
I _H	I _T =100mA		MAX	50	25	mA

JST12 Series

dV/dt	$V_D=2/3V_{DRM}$ Gate Open $T_j=125^\circ\text{C}$	MIN	400	200	V/ μs
(dV/dt) _c	without snubber $T_j=125^\circ\text{C}$	MIN	/	/	V/ μs

STATIC CHARACTERISTICS

Symbol	Parameter		Value(MAX)	Unit
V_{TM}	$I_{TM}=17\text{A}$ $t_p=380\mu\text{s}$	$T_j=25^\circ\text{C}$	1.55	V
I_{DRM}	$V_D=V_{DRM}$ $V_R=V_{RRM}$	$T_j=25^\circ\text{C}$	5	μA
I_{RRM}		$T_j=125^\circ\text{C}$	1	mA

THERMAL RESISTANCES

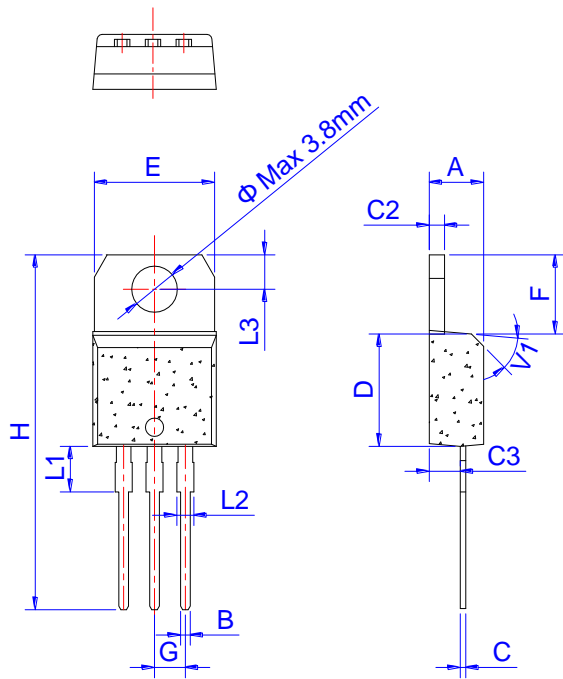
Symbol	Parameter		Value	Unit
$R_{th(j-c)}$	junction to case(AC)	TO-220A(Ins)	2.3	$^\circ\text{C/W}$
		TO-220B(Non-Ins)/ TO-220C	1.4	
		TO-220F(Ins)	3.9	
		TO-263	0.95	

ORDERING INFORMATION

JieJie Microelectronics Co.,Ltd	J	ST	12	A	-600	BW
	Triacs	$I_{T(RMS)}:12\text{A}$	A:TO-220A(Ins) F:TO-220F(Ins) B:TO-220B(Non-Ins) C:TO-220C E:TO-263			BW: $I_{GT1-3}\leq 50\text{mA}$ CW: $I_{GT1-3}\leq 35\text{mA}$ SW: $I_{GT1-3}\leq 10\text{mA}$ TW: $I_{GT1-3}\leq 5\text{mA}$ B: $I_{GT1-3}\leq 50\text{mA}$ $I_{GT4}\leq 70\text{mA}$ C: $I_{GT1-3}\leq 25\text{mA}$ $I_{GT4}\leq 50\text{mA}$
					600: $V_{DRM}/V_{RRM}\geq 600\text{V}$ 800: $V_{DRM}/V_{RRM}\geq 800\text{V}$ 1200: $V_{DRM}/V_{RRM}\geq 1200\text{V}$	

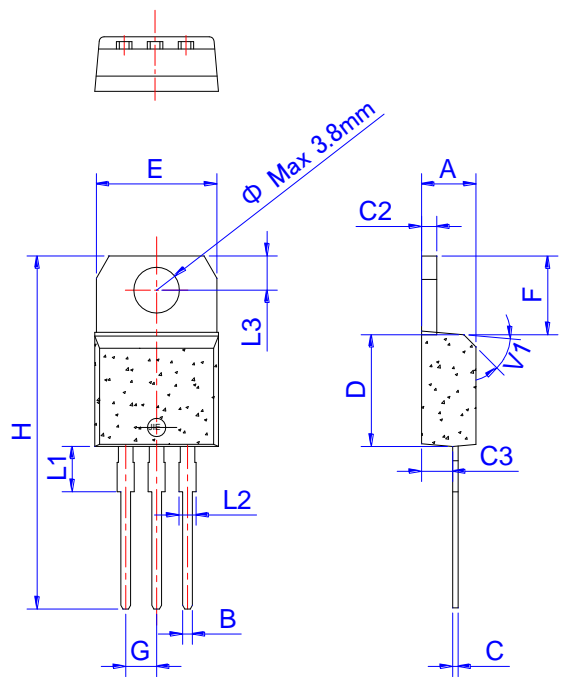
JST12 Series

PACKAGE MECHANICAL DATA



TO-220A Ins

Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	4.40		4.60	0.173		0.181
B	0.61		0.88	0.024		0.035
C	0.46		0.70	0.018		0.028
C2	1.21		1.32	0.048		0.052
C3	2.40		2.72	0.094		0.107
D	8.60		9.70	0.339		0.382
E	9.80		10.4	0.386		0.409
F	6.55		6.95	0.258		0.274
G		2.54			0.1	
H	28.0		29.8	1.102		1.173
L1		3.75			0.148	
L2	1.14		1.70	0.045		0.067
L3	2.65		2.95	0.104		0.116
V1		45°			45°	

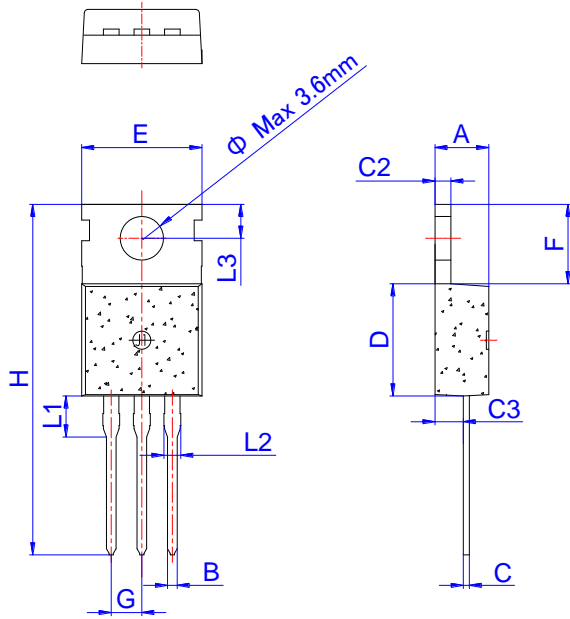


TO-220B Non-Ins

Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	4.40		4.60	0.173		0.181
B	0.61		0.88	0.024		0.035
C	0.46		0.70	0.018		0.028
C2	1.21		1.32	0.048		0.052
C3	2.40		2.72	0.094		0.107
D	8.60		9.70	0.339		0.382
E	9.60		10.4	0.378		0.409
F	6.20		6.60	0.244		0.260
G		2.54			0.1	
H	28.0		29.8	1.102		1.173
L1		3.75			0.148	
L2	1.14		1.70	0.045		0.067
L3	2.65		2.95	0.104		0.116
V1		45°			45°	

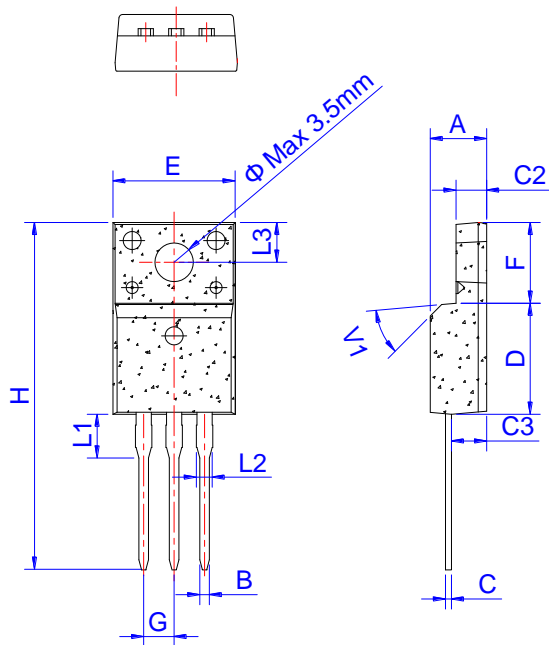
JST12 Series

PACKAGE MECHANICAL DATA



TO-220C

Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	4.40		4.60	0.173		0.181
B	0.70		0.90	0.028		0.035
C	0.45		0.60	0.018		0.024
C2	1.23		1.32	0.048		0.052
C3	2.20		2.60	0.087		0.102
D	8.90		9.90	0.350		0.390
E	9.90		10.3	0.390		0.406
F	6.30		6.90	0.248		0.272
G		2.54			0.1	
H	28.0		29.8	1.102		1.173
L1		3.39			0.133	
L2	1.14		1.70	0.045		0.067
L3	2.65		2.95	0.104		0.116
Φ		3.6			0.142	

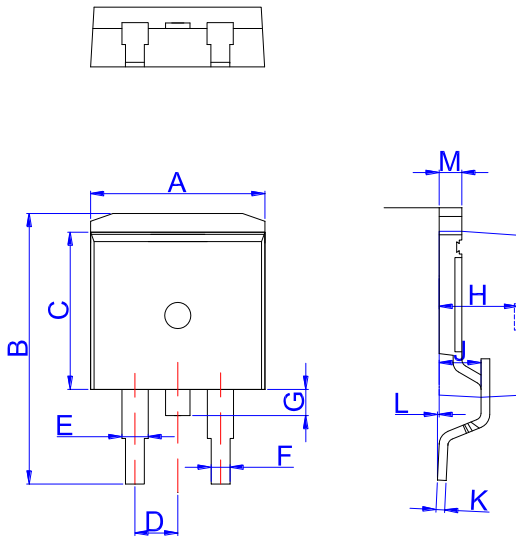


TO-220F Ins

Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	4.40		4.80	0.173		0.189
B	0.74	0.80	0.83	0.029	0.031	0.033
C	0.48		0.75	0.019		0.030
C2	2.40		2.70	0.094		0.106
C3	2.60		3.00	0.102		0.118
D	8.80		9.30	0.346		0.366
E	9.70		10.3	0.382		0.406
F	6.40		7.00	0.252		0.276
G		2.54			0.1	
H	28.0		29.8	1.102		1.173
L1		3.63			0.143	
L2	1.14		1.70	0.045		0.067
L3		3.30			0.130	
V1		45°			45°	

JST12 Series

PACKAGE MECHANICAL DATA



TO-263

Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	9.90		10.20	0.390		0.402
B	14.70		15.80	0.579		0.622
C	9.4		9.6	0.37		0.378
D		2.54			0.100	
E	1.20		1.40	0.047		0.055
F	0.75		0.85	0.029		0.033
G			1.75			0.069
H	4.40		4.70	0.173		0.185
J	2.30		2.70	0.091		0.106
K	0.38		0.55	0.015		0.022
L	0	0.10	0.25	0	0.004	0.010
M	1.25		1.35	0.049		0.053

FIG.1 Maximum power dissipation versus RMS on-state current

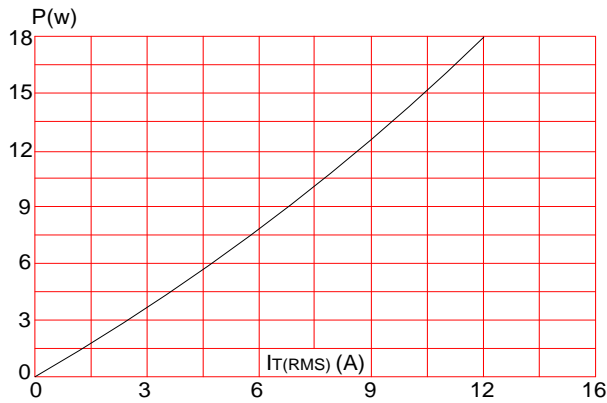


FIG.3: Surge peak on-state current versus number of cycles

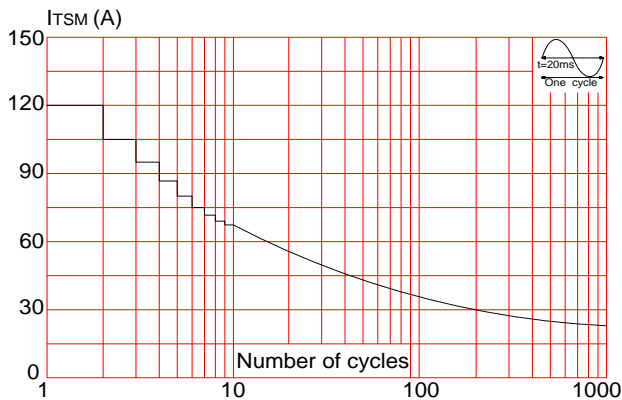


FIG.2: RMS on-state current versus case temperature

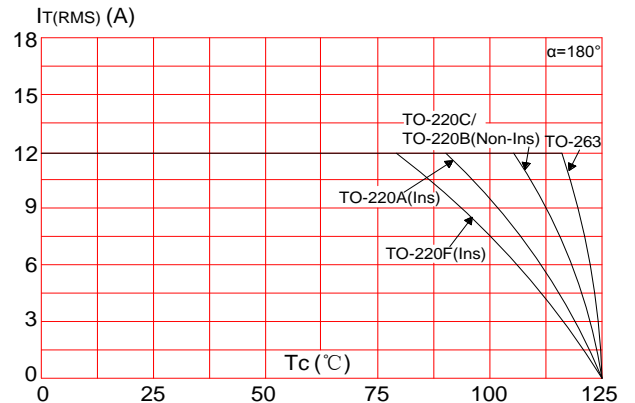
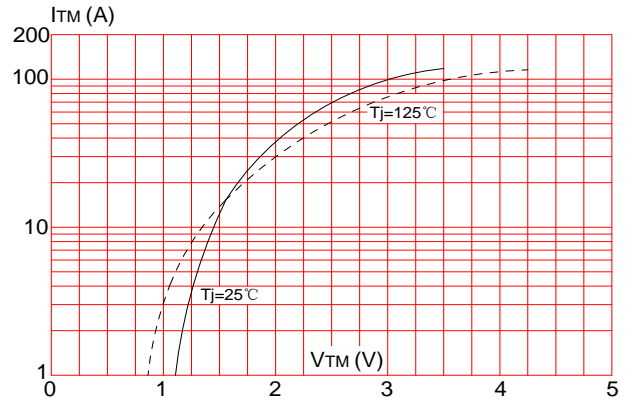


FIG.4: On-state characteristics (maximum values)



JST12 Series

FIG.5: Non-repetitive surge peak on-state current for a sinusoidal pulse with width $t_p < 20\text{ms}$, and corresponding value of I^2t ($di/dt < 50\text{A}/\mu\text{s}$)

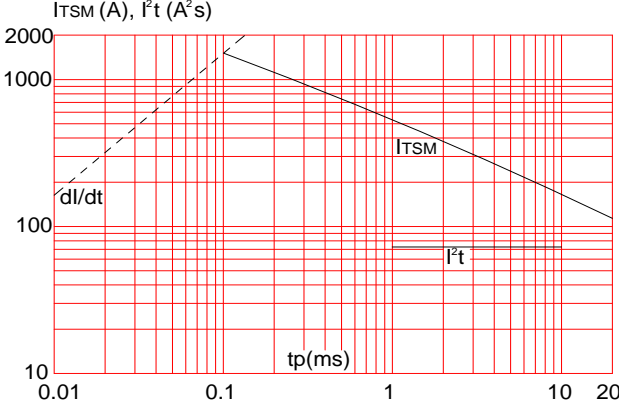


FIG.6: Relative variations of gate trigger current, holding current and latching current versus junction temperature

